

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2221	((438/167) or (438/172) or (438/300) or (438/752) or (438/753)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 15:33
L2	29410	silicon near2 germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
L3	496	"si.sub.x ge.sub.1-x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
L4	330	"si.sub.xge.sub.1-x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
L5	53	"si.sub.x ge.sub.y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
L6	65	"si.sub.y ge.sub.1-y" "si.sub.yge.sub.1-y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
L7	910	"si.sub.1-x ge.sub.x" "si.sub.1-xge.sub.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
L8	158	"si.sub.1-y ge.sub.y" "si.sub.1-yge.sub.y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
L9	284706	tensile	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33

L10	1600199	compress\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
L11	9199	sige gesi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
L12	35139	L3 or L4 or L5 or L6 or L7 or L8 or L2 or L11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
L13	184	L12 same strain\$4 same L9 same L10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
L14	132	amberwave.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
L15	88	13 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:34
L16	78	15 not 14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:34
L17	10	15 and 14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:34
S96	5	US-5442205-\$.DID. OR US-5726087-\$.DID. OR US-5780922-\$.DID. OR US-6107653-\$.DID. OR US-6284615-\$.DID.	USPAT	OR	OFF	2005/04/29 16:30
S97	2	(("20020068393") or ("200302302333") or ("20040031979")).PN.	US-PGPUB; USOCR	OR	OFF	2005/04/29 16:31
S98	3	(("20020068393") or ("20030230233") or ("20040031979")).PN.	US-PGPUB; USOCR	OR	OFF	2005/04/29 16:49

S99	1	("20020197803").PN.	US-PGPUB; USOCR	OR	OFF	2005/04/29 18:16
S10 0	21737	coffee	USPAT	OR	OFF	2005/04/29 18:16
S10 1	210	brewster-william-m.xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:47
S10 2	29374	silicon near2 germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:49
S10 3	19	S101 and S102	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:47
S10 4	45096	silicon near2 germanium si near2 ge "si.sub.xge.sub.y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:50
S10 5	494	"si.sub.x ge.sub.1-x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:51
S10 6	330	"si.sub.xge.sub.1-x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:50
S10 7	53	"si.sub.x ge.sub.y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:50
S10 8	65	"si.sub.y ge.sub.1-y" "si.sub.yge. sub.1-y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:51
S10 9	909	"si.sub.1-x ge.sub.x" "si.sub.1-xge. sub.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:51

S11 0	158	"si.sub.1-y ge.sub.y" "si.sub.1-yge. sub.y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:52
S11 1	29960	S105 or S106 or S107 or S108 or S109 or S110 or S102	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:10
S11 2	284587	tensile	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:53
S11 3	1599544	compress\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:53
S11 4	2929508	insulat\$4 dielectric oxide nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:12
S11 5	173201	implant or implant or implanting or implanting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 12:43
S11 6	237	S111 and S112 and S113 and S114 and S115	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:05
S11 7	111	S116 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:05
S11 8	28494	soi silicon adj on adj insulator silicon-on-insulator	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:59
S12 0	71	S117 and S118	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:02

S12 1	9184	sige gesi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:02
S12 2	35096	S105 or S106 or S107 or S108 or S109 or S110 or S102 or S121	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:02
S12 3	184	S122 same strain\$4 same S112 same S113	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
S12 4	63	S123 and S114 and S115 and S118	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:39
S12 5	15	S124 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:35
S12 6	34	S123 and S114 same S115 and S118	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:38
S12 7	4	S126 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:39
S12 8	13	S123 and S114 with S115	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:41
S12 9	1	S128 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:42
S13 0	2054	S122 and S114 with S115	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:42

S13 1	98	S122 and S114 with S115 and S112 and S113	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:42
S13 2	54	S131 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:43
S13 3	13	S114 with S115 and (S112 same S113 same S122)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:42
S13 4	1	S133 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:43
S13 5	29374	silicon near2 germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:10
S13 6	494	"si.sub.x ge.sub.1-x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:10
S13 7	330	"si.sub.xge.sub.1-x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:10
S13 8	53	"si.sub.x ge.sub.y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:10
S13 9	65	"si.sub.y ge.sub.1-y" "si.sub.yge. sub.1-y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:10
S14 0	909	"si.sub.1-x ge.sub.x" "si.sub.1-xge. sub.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:10

S14 1	158	"si.sub.1-y ge.sub.y" "si.sub.1-yge. sub.y"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:10
S14 2	29960	S136 or S137 or S138 or S139 or S140 or S141 or S135	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:10
S14 3	21118	strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:19
S14 4	3253129	insulat\$4 dielectric oxide nitride mask\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:12
S14 5	173201	inplant or implant or inplanting or implanting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:16
S14 6	37398	S144 with S145	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:16
S14 7	299	S142 and S143 and S146	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:19
S14 8	131	S147 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:20
S14 9	132	amberwave.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33
S15 1	122	S148 not S149	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:18

S15 2	1039	strained with tensile\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:19
S15 3	849	strained with compressive\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:19
S15 4	21	S142 and S152 and S153 and S146	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:20
S15 5	6	S154 and (@ad < "20021030")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:34
S15 6	2	S155 not S149	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 18:01
S15 7	2	"20020171077".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 12:43
S15 8	1	S157 and (soi or silicon adj on adj insulat\$4 or silicon-on-insulat\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 13:43
S15 9	2	(angstrom ang ang? nm nanometer) and S157	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 18:05
S16 0	2	"20020171077".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 12:43
S16 1	173324	inplant or implant or inplanting or implanting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 12:43



S16 2	2	"20020171077".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 13:44
S16 3	1	S162 and (rta rtp anneal\$6 cvd chemical\$4 adj vapor adj depositi\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 14:12
S16 4	1186	rapid adj thermal\$4 adj oxidat\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 14:13
S16 5	1096	rapid adj thermal\$4 adj oxidat\$6	US-PGPUB; USPAT	OR	ON	2005/05/03 14:13